

40 Volt, 10 Amp Peak, High-Frequency, Integrated Laser Driver

Description

The EPC21603 is a laser driver that is controlled using LVDS logic at high frequencies of up to 100 MHz to modulate laser driving currents of up to 10 Amps. Full driver integration is achieved using EPC's proprietary GaN IC technology.

Wafer level chip-scale packaging is used resulting in a BGA package that measures only 1.5 mm x 1 mm x 0.68 mm. The BGA package has low inductance and lays out very well with the laser system.



1.5 mm x 1 mm, 0.5 mm pitch Bump side view

The EPC21603 uses a 5 V logic supply and is capable of interfacing to digital controllers. It can switch at frequencies exceeding 100 MHz.

Features

- V_{Laser} operating range up to 30 V
- 10 Amp peak current
- Switching frequency greater than 100 MHz
- Voltage switching time less than 500 ps
- 5 V nominal logic power supply
- LVDS logic compatible input control
- 2 ns minimum input pulse width
- 2.9 ns delay time from input to output



Functional Block Diagram

Applications

- Time of flight measurement
 - Gesture recognition
 - o Gaming
 - Driver monitoring
 - o Robotic vision
 - Vacuum cleaners
 - Industrial safety
 - o Machine vision
- ToF module using VCEL laser for camera modules, laptops and smart phones



Typical Connection Diagram



Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to GND unless indicated otherwise.

Symbol	Symbol Definition		Max	Units
VD	Drain Voltage		40	V
V _{DD}	Low Side Supply Voltage (V _{DD} to GND)	-0.3	5.5	V
IN	Logic Input	-0.3	5	V
ID	Average Drain Current		1.7	А
TJ	Junction Temperature	-40	150	°C
T _{STG}	Storage Temperature	-40	150	°C

ESD Ratings

(Testing performed at EAG Lab. Need to get the relevant JEDEC specs for ESD ratings)

Symbol	Definition	Min	Units
НВМ	Human-body model	+/-1000	V
CDM	Charged-device model	+/-500	V

Thermal Characteristics

 $R_{\theta JA}$ is determined with the device mounted on one square inch of copper pad, single layer 2 oz copper on FR4 board.

Symbol	Definition	Тур	Units
R _{θJC}	Thermal Resistance, Junction to Case	TBD	°C/W
R _{θJB}	Thermal Resistance, Junction to Board	TBD	°C/W



EPC21603 – 40 V, 10 A eToF™ Laser Driver IC – PRELIMINARY

R _{θJA}	Thermal Resistance, Junction to Ambient	TBD	°C/W

Recommended Operating Conditions

For proper operation, the device should be used within the recommended conditions. All voltage parameters are absolute voltages referenced to GND unless indicated otherwise.

Symbol	Definition	Min	Тур	Max	Units
V _{Laser}	Input Voltage (V _{IN} to GND)	10		30	V
V _{DD}	Logic Supply Voltage		5		V

Truth Table

IN	Laser
IN+ ≤ IN-	Off
IN+ > IN-	On

Electrical Characteristics

All ratings at T_J = 25 °C. V_{Laser} = 15 V, I_D = 5 A, V_{IL} = 0 V, V_{IH} = 3.3 V, V_{DD} = 5 V, R_D = 100 Ω unless indicated otherwise.

Symbol	Definition		Тур	Max	Units
Operating Po	ower Supply, V _{DD}			-	
I _{DD (Off)}	V _{DD} Quiescent current with laser driver off		10.5	12.5	mA
IDD (30 MHz)	Operating current off V _{DD}		47	58	mA
Input Pins				-	
V _{ITH+}	Positive-going differential input voltage			100	mV
	threshold, T_J = -40 °C to 150 °C				
VITH-	Negative-going differential input voltage	-100			mV
	threshold, T _J = -40 °C to 150 °C				
R _C	Common-mode input resistance to 1.2 V		2.5		kΩ
Power Stage					
R _{DS(on)}	Drain to Source Resistance		40.5	54.0	mΩ
I _{D(peak)}	Peak Laser Drive Current Capability	10			Α
Coss	V _{DS} = 20 V		45		рF
Q _{OSS}	V _{DS} = 20 V		1.4		nC
Eoss	V _{DS} = 20 V		15		nJ



EPC21603 – 40 V, 10 A eToF™ Laser Driver IC – PRELIMINARY

Dynamic Characteristics					
t _{D(on)}	Turn on delay time		3.5	4.5	ns
t _F	Drain fall time		0.41	0.6	ns
t _{D(off)}	Turn off delay time		3.1	4.0	ns
t _R	Drain rise time *		0.32	0.5	ns
t _{dPW}	Pulse width distortion	-0.7	-0.4	-0.2	ns
t _{in(min(on))}	Minimum input pulse width		2.5		ns
t _{On(Max)}	Maximum on time		500		ns
t _{Off(Max)}	Maximum off time $V_D < 10 V$		100		μs

Pinout Description

Pin	Description
V _{DD}	Input Voltage Supply (Decouple to GND with small, low inductance capacitor)
In+	Differential (LVDS) non-inverting output
In-	Differential (LVDS) inverting output
D	Power Drain
GND	Power and Signal Ground





Application Information

<u>Layout and decoupling</u>: Minimizing inductance in both power and gate drive loops is critical. The power loop is primary, and gate drive loop secondary. Short, wide traces are required, and returning in the second layer, using a thin dielectric will cancel much of the inductance. Using multiple ceramic capacitors in parallel will reduce stray inductance and impedance in the power loop. Use high quality NPO or COG capacitors for both power and gate drive. This will increase effective capacitance as capacitors with lower quality materials will lose much more capacitance with voltage. Recommended layout is shown below. Component recommendations for power and gate drive decoupling capacitors are shown in the <u>demonstration board</u> quick start guide.

Turn off current is limited by the energy of the power loop stray inductance transferring to the C_{OSS} of the power FET of the laser driver. E_{OSS} versus V_{DS} curve is in the datasheet.



Cathode to drain connection on second conductor layer.

<u>Start up</u>: V_{DD} should be applied before the laser voltage. For applications where the laser voltage is below 10 V, it may take a few pulses before the pulse width stabilizes. For correct measurement, it may be necessary to ignore the first few pulses.

<u>Input logic</u>: LVDS inputs are used with each input internally pulled to 1.2 V with 2.5 k Ω . For safety IN+ should be pulled to ground with 1 k Ω and IN- should be pulled to V_{DD} with 3 k Ω .



Parameter Measurement Test Circuits



Parameter Measurement Definitions





Die Outline (solder bump view)



	м	ICROMETE	RS
DIN	MIN	Nominal	ΜΑΧ
Α	1420	1450	1480
В	920	950	980
с		500	
d		500	
е	238	264	290

Pad 1 is IN+ Pad 2 is IN-Pad 3 is Drain Pad 4 is VDD

Pads 5, 6 are Source

Side View



Recommended Land Pattern



The land pattern is solder mask defined Solder mask is 10µm smaller per side than bump

DIM	MICROMETERS
Α	1450
В	950
с	500
d	500
е	230

Pad 1 is IN+ Pad 2 is IN-

Pad 3 is Drain Pad 4 is VDD

Pads 5, 6 are Source

Recommended Stencil Drawing

(measurements in µm)



Recommended stencil should be 4mil (100 μm) thick, must be laser cut , opening per drawing. The corner has a radius of R60

Intended for use with SAC305 Type 4 solder, reference 88.5% metals content.

Additional assembly resources are available at:

epc-co.com/epc/DesignSupport/AssemblyBasics.aspx



Die Marking



Tape and Reel Configuration

4mm pitch, 8mm wide tape on 7" reel



Efficient Power Conversion Corporation (EPC) reserves the right to make changes without further notice to any products herein. Preliminary specification sheet contains informaton regarding a product EPC is considering for production release. EPC does not assume any liability arising out of the application or use of any product or circuit described herin; neither does it convey any license under its patent rights, nor the rights of other.

eGaN[°] is a registered trademark of Efficient Power Conversion Corporation.

EPC Patents: http://epc-co.com/epc/AboutEPC/Patents.aspx

Revised March 18, 2021

Subject to Change without Notice www.epc-co.com

COPYRIGHT 2021